

512Kx16 SRAM MODULE

FEATURES

- Access Times 17, 20, 25, 35ns
- MIL-STD-883 Compliant Devices Available
- Packaging
 - 44 pin Ceramic SOJ (Package 102)
 - 44 lead Ceramic Flatpack (Package 209)
- Organized as two banks of 256Kx16
- Data Byte Control:
 - Lower Byte (LB#) = I/O1-8
 - Upper Byte (UB#) = I/O9-16
- Data I/O Compatible with 3.3V devices
- 2V Minimum Data Retention for battery back up operation
- Commercial, Industrial and Military Temperature Range
- 5 Volt Power Supply (3.3V parts also available)
- Low Power CMOS
- TTL Compatible Inputs and Outputs

* This product is under development, is not qualified or characterized and is subject to change or cancellation without notice.

PIN CONFIGURATION FOR WS512K16-XXX

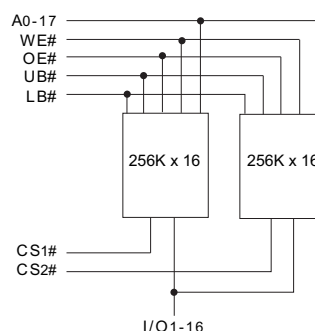
44 CSOJ 44 FLATPACK Top View

A0	1	44	A17
A1	2	43	A16
A2	3	42	A15
A3	4	41	OE#
A4	5	40	UB#
CS1#	6	39	LB#
I/O1	7	38	I/O16
I/O2	8	37	I/O15
I/O3	9	36	I/O14
I/O4	10	35	I/O13
Vcc	11	34	GND
GND	12	33	Vcc
I/O5	13	32	I/O12
I/O6	14	31	I/O11
I/O7	15	30	I/O10
I/O8	16	29	I/O9
WE#	17	28	CS2#
A5	18	27	A14
A6	19	26	A13
A7	20	25	A12
A8	21	24	A11
A9	22	23	A10

Pin Description

A0-17	Address Inputs
LB#	Lower-Byte Control (I/O1-8)
UB#	Upper-Byte Control (I/O9-16)
I/O1-16	Data Input/Output
CS1-2#	Chip Select
OE#	Output Enable
WE#	Write Enable
Vcc	+5.0V Power
GND	Ground
NC	No Connection

Block Diagram





TRUTH TABLE

CS1#	CS2#	WE#	OE#	LB#	UB#	Mode	Data I/O		Power
H	H	X	X	X	X	Not Select	I/O1-8	I/O9-16	Standby
L	H	H	H	X	X	Output Disable	High Z	High Z	Active
H	L								
L	H	X	X	H	H				
H	L								
H	L	H	L	L	H	Read	Data Out	High Z	Active
L	H			H	L		High Z	Data Out	
				L	L		Data Out	Data Out	
H	L	L	H	L	H	Write	Data In	High Z	Active
L	H			H	L		High Z	Data In	
				L	L		Data In	Data In	

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Min	Max	Unit
Operating Temperature	T _A	-55	+125	°C
Storage Temperature	T _{STG}	-65	+150	°C
Signal Voltage Relative to GND	V _G	-0.5	V _{CC} +0.5	V
Junction Temperature	T _J		150	°C
Supply Voltage	V _{CC}	-0.5	7.0	V

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V _{CC}	4.5	5.5	V
Input High Voltage	V _{IH}	2.2	V _{CC} + 0.3	V
Input Low Voltage	V _{IL}	-0.3	+0.8	V
Operating Temp. (MIL)	T _A	-55	+125	°C

CAPACITANCE

T_A = +25°C

Parameter	Symbol	Conditions	Max	Unit
Input capacitance	C _{IN}	V _{IN} = 0V, f = 1.0 MHz	25	pF
Output capacitance	C _{OUT}	V _{OUT} = 0V, f = 1.0 MHz	25	pF

This parameter is guaranteed by design but not tested.

DC CHARACTERISTICS

V_{CC} = 5.0V, V_{SS} = 0V, -55°C ≤ T_A ≤ +125°C

Parameter	Sym	Conditions	Min	Max	Units
Input Leakage Current	I _{LI}	V _{CC} = 5.5, V _{IN} = GND to V _{CC}		10	μA
Output Leakage Current	I _{LO}	CS# = V _{IH} , OE# = V _{IH} , V _{OUT} = GND to V _{CC}		10	μA
Operating Supply Current	I _{CC}	CS# = V _{IL} , OE# = V _{IH} , f = 5MHz, V _{CC} = 5.5		290	mA
Standby Current	I _{SB}	CS# = V _{IH} , OE# = V _{IH} , f = 5MHz, V _{CC} = 5.5		30	mA
Output Low Voltage	V _{OL}	I _{OL} = 8mA, V _{CC} = 4.5		0.4	V
Output High Voltage	V _{OH}	I _{OH} = -4.0mA, V _{CC} = 4.5	2.4		V

NOTE: DC test conditions: V_{IH} = V_{CC} - 0.3V, V_{IL} = 0.3V

DATA RETENTION CHARACTERISTICS

-55°C ≤ T_A ≤ +125°C

Characteristic	Sym	Conditions	Min	Typ	Max	Units
Data Retention Supply Voltage	V _{DR}	CS# ≥ V _{CC} - 0.2V	2.0		5.5	μA
Data Retention Current	I _{CCDR1}	V _{CC} = 3V		2.0	12.0*	mA

* Also available in Low Power version. Please call factory for information.



AC CHARACTERISTICS

 $V_{CC} = 5.0V$, $GND = 0V$, $-55^{\circ}C \leq T_A \leq +125^{\circ}C$

Parameter Read Cycle	Symbol	-17		-20		-25		-35		Units
		Min	Max	Min	Max	Min	Max	Min	Max	
Read Cycle Time	t_{RC}	17		20		25		35		ns
Address Access Time	t_{AA}		17		20		25		35	ns
Output Hold from Address Change	t_{OH}	0		0		0		0		ns
Chip Select Access Time	t_{ACS}		17		20		25		35	ns
Output Enable to Output Valid	t_{OE}		10		12		15		20	ns
Chip Select to Output in Low Z	t_{CLZ}^1	2		5		5		5		ns
Output Enable to Output in Low Z	t_{OLZ}^1	0		0		0		0		ns
Chip Disable to Output in High Z	t_{CHZ}^1		9		10		12		15	ns
Output Disable to Output in High Z	t_{OHZ}^1		9		10		12		15	ns
LB#, UB# Access Time	t_{BA}		10		12		14		17	ns
LB#, UB# Enable to Low Z Output	t_{BLZ1}	0		0		0		0		ns
LB#, UB# Disable to High Z Output	t_{BHZ1}		9		10		12		15	ns

1. This parameter is guaranteed by design but not tested.

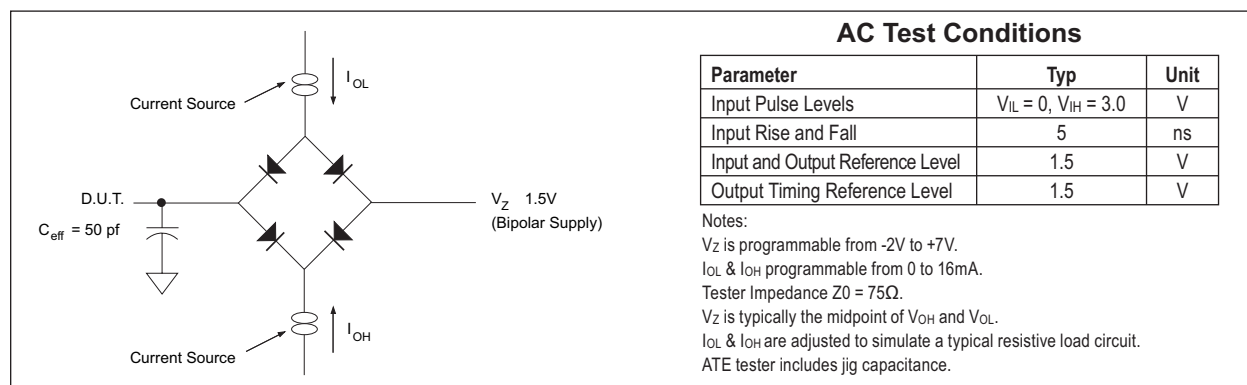
AC CHARACTERISTICS

 $V_{CC} = 5.0V$, $GND = 0V$, $-55^{\circ}C \leq T_A \leq +125^{\circ}C$

Parameter Write Cycle	Symbol	-17		-20		-25		-35		Units
		Min	Max	Min	Max	Min	Max	Min	Max	
Write Cycle Time	t_{WC}	17		20		25		35		ns
Chip Select to End of Write	t_{CW}	14		17		20		25		ns
Address Valid to End of Write	t_{AW}	14		17		20		25		ns
Data Valid to End of Write	t_{DW}	10		12		15		20		ns
Write Pulse Width	t_{WP}	14		17		20		25		ns
Address Setup Time	t_{AS}	0		0		0		0		ns
Address Hold Time	t_{AH}	0		0		0		0		ns
Output Active from End of Write	t_{OW}^1	0		0		0		0		ns
Write Enable to Output in High Z	t_{WHZ}^1		9		10		10		15	ns
Data Hold Time	t_{DH}	0		0		0		0		ns
LB#, UB# Valid to End of Write	t_{BW}	14		17		20		25		ns

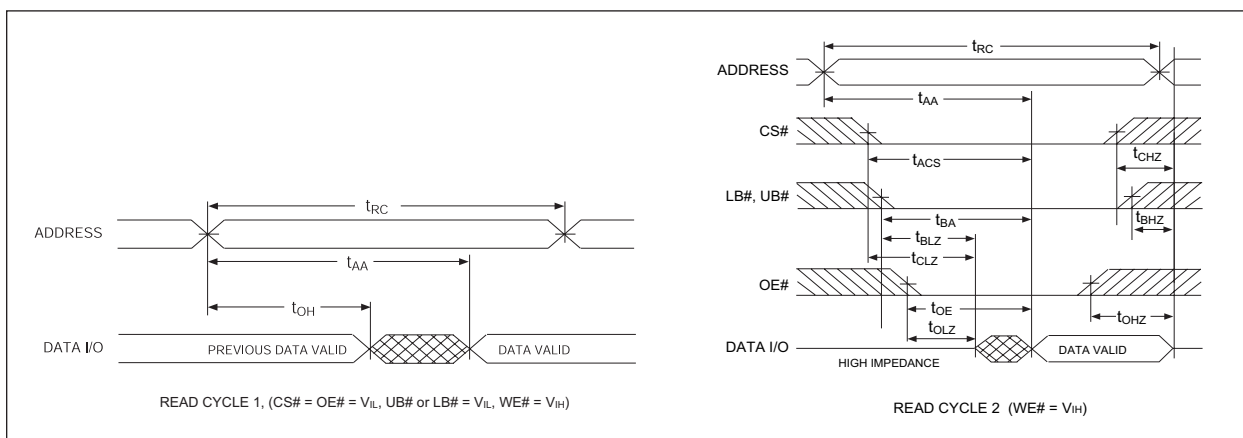
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AC TEST CIRCUIT

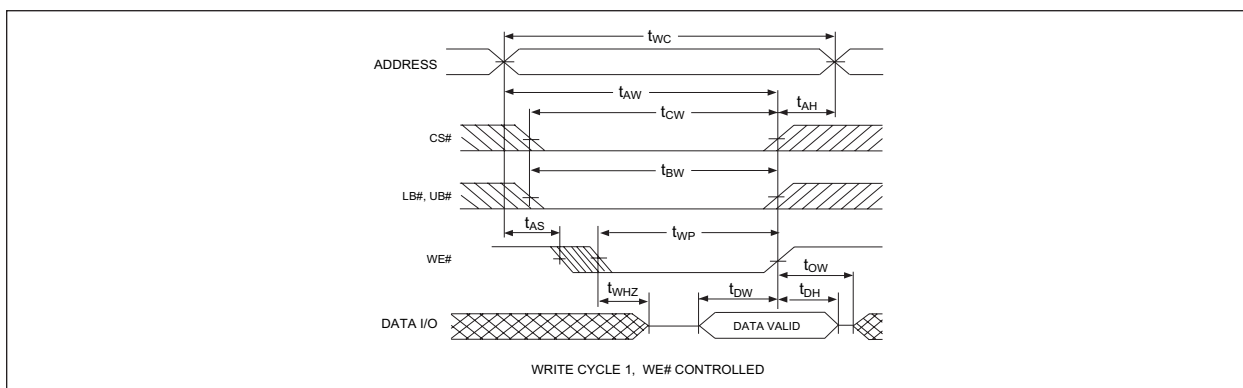




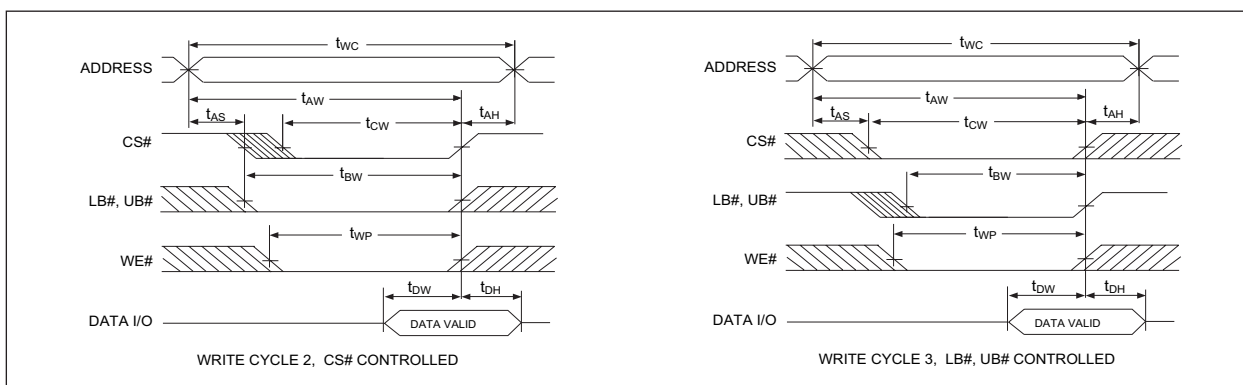
TIMING WAVEFORM – READ CYCLE



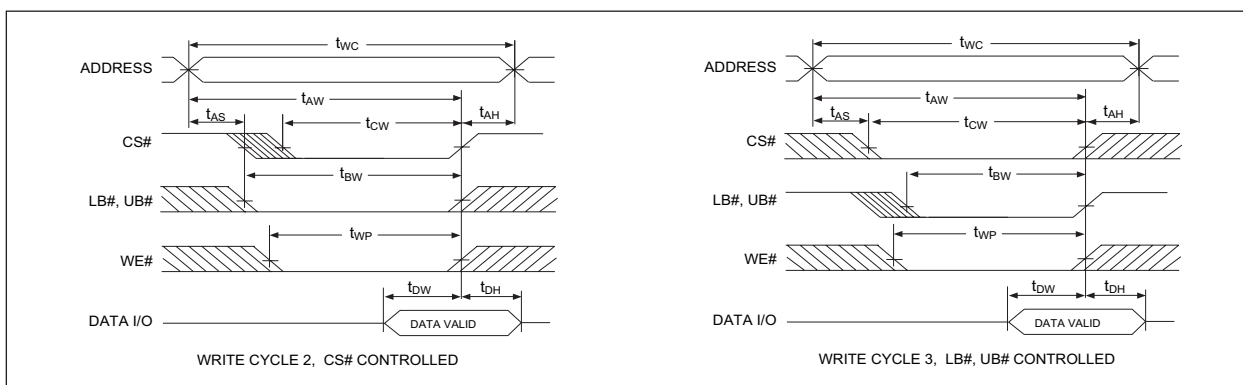
WRITE CYCLE – WE# CONTROLLED



WRITE CYCLE – CS# CONTROLLED

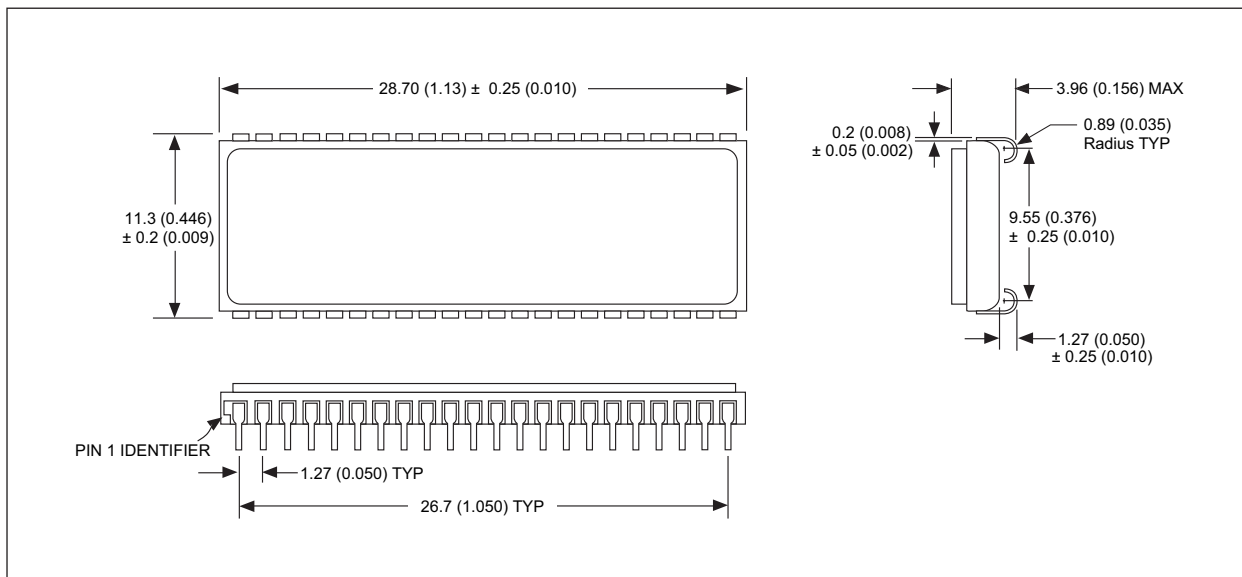


WRITE CYCLE – LB#, UB# CONTROLLED



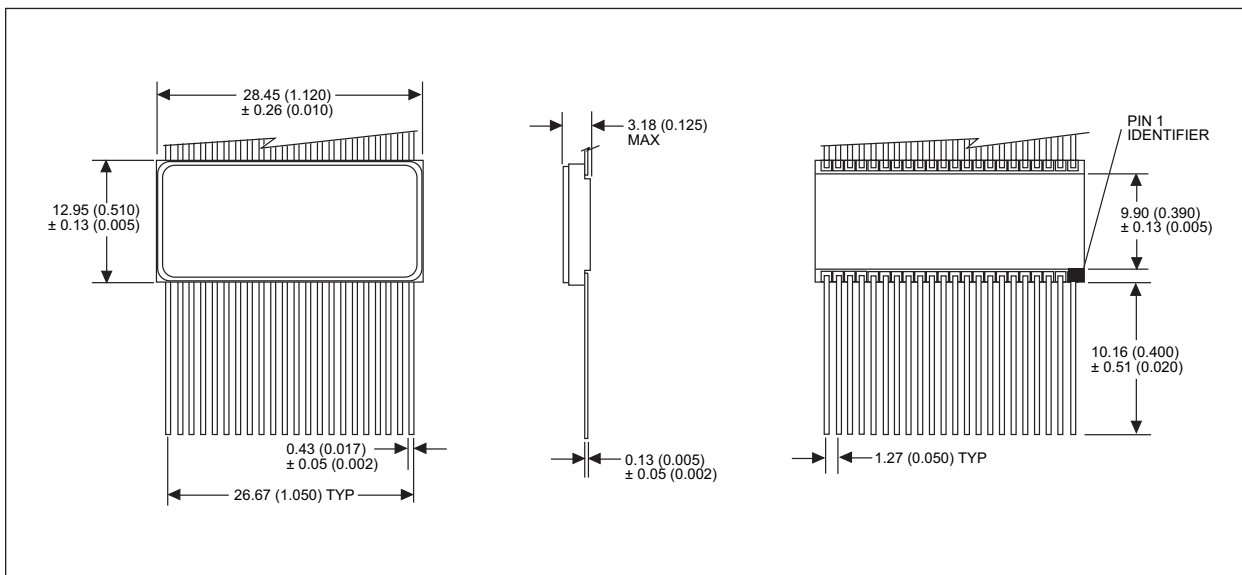


PACKAGE 102: 44 LEAD, CERAMIC SOJ



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES

PACKAGE 209: 44 LEAD, CERAMIC FLAT PACK



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES



WHITE ELECTRONIC DESIGNS

WS512K16-XXX

ADVANCED

ORDERING INFORMATION

